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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

SAH
#2A
7-9.01

IN RE APPLICATION OF YOUNG HOON PARK

FOR: REACTOR FOR DEPOSITING THIN FILM ON WAFER

PRELIMINARY AMENDMENT

The Assistant Commissioner of
Patents and Trademarks
Washington, DC 20231

Dear Sir:

Before examining the present application, please amend as follows:

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IN THE SPECIFICATION:

Please accept the following specification paragraph in re-written "clean form". The
following paragraph is the last paragraph on the first page of the specification.

--To achieve the above objective, the present invention provides a thin film
deposition reactor including a reactor block on which a wafer is placed, a shower head
plate for uniformly maintaining a predetermined pressure by covering the reactor block, a
wafer block installed in the reactor block, on which the wafer is to be seated, and an
exhausting portion connected to the reactor block for exhausting a gas from the reactor
block. The thin film deposition reactor further includes: a first connection line in
communication with the shower head plate, through which a first reaction gas and/or inert
gas flow; a second connection line in communication with the shower head plate, through
which a second reaction gas and/or inert gas flow; and a diffusion plate mounted on a
lower surface of the shower head plate. This diffusion plate has a plurality of spray holes
which are in communication with the first connection line and face the upper surface of
the wafer to spray the first reaction gas and/or inert gas onto the wafer, and a plurality of